# Features

- **Serial Peripheral Interface (SPI) Compatible**
- **Supports SPI Modes 0 (0,0) and 3 (1,1)**
- **2.1 MHz Clock Rate**
- **128-byte Page Mode Only for Write Operations**
- **Low-voltage and Standard-voltage Operation**
  - **2.7 (V_{CC} = 2.7V to 5.5V)**
- **Block Write Protection**
  - **Protect 1/4, 1/2, or Entire Array**
- **Write Protect ($\overline{WP}$) Pin and Write Disable Instructions for Both Hardware and Software Data Protection**
- **Self-Timed Write Cycle (5 ms Typical)**
- **High Reliability**
  - **Endurance: 100,000 Write Cycles**
  - **Data Retention: >40 Years**
- **20-lead JEDEC SOIC and 8-lead Leadless Array Package**

Description

The AT25P1024 provides 1,048,576 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 131,072 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low power and low voltage operation are essential. The AT25P1024 is available in space saving 20-lead JEDEC SOIC and 8-lead LAP packages.

Table 1. Pin Configurations

Pin Name	Function
$\overline{CS}$	Chip Select
SCK	Serial Data Clock
SI	Serial Data Input
SO	Serial Data Output
GND	Ground
VCC	Power Supply
$\overline{WP}$	Write Protect
$\overline{HOLD}$	Suspends Serial Input
NC	No Connect

20-lead SOIC

```
 CS  [ 1        20 ]  VCC
 SO  [ 2        19 ]  HOLD
 NC  [ 3        18 ]  NC
 NC  [ 4        17 ]  NC
 NC  [ 5        16 ]  NC
 NC  [ 6        15 ]  NC
 NC  [ 7        14 ]  NC
 NC  [ 8        13 ]  NC
 WP  [ 9        12 ]  SCK
 GND [ 10       11 ]  SI
```

8-lead Leadless Array

```
 VCC  [8]      [1]  CS
 HOLD [7]      [2]  SO
 SCK  [6]      [3]  WP
 SI   [5]      [4]  GND
```
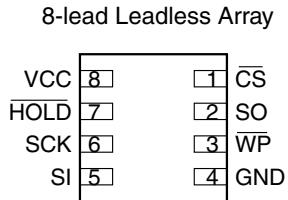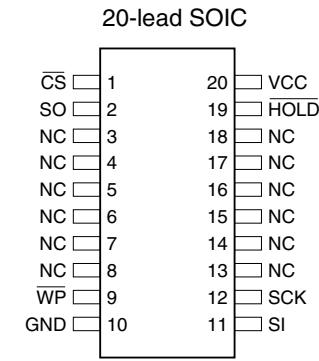
Bottom View

The AT25P1024 is enabled through the Chip Select pin ($\overline{CS}$) and accessed via a 3-wire interface consisting of Serial Data Input (SI), Serial Data Output (SO), and Serial Clock (SCK). All programming cycles are completely self-timed, and no separate erase cycle is required before write.

Block Write protection is enabled by programming the status register with top ¼, top ½ or entire array of write protection. Separate Program Enable and Program Disable instructions are provided for additional data protection. Hardware data protection is provided via the $\overline{WP}$ pin to protect against inadvertent write attempts to the status register. The $\overline{HOLD}$ pin may be used to suspend any serial communication without resetting the serial sequence.

Absolute Maximum Ratings*

Operating Temperature................................... -55°C to +125°C	
Storage Temperature .... -65°C to +150°C	
Voltage on Any Pin with Respect to Ground ....-1.0V to +7.0V	
Maximum Operating Voltage 6.25V	
DC Output Current.. 5.0 mA	

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 1. Block Diagram
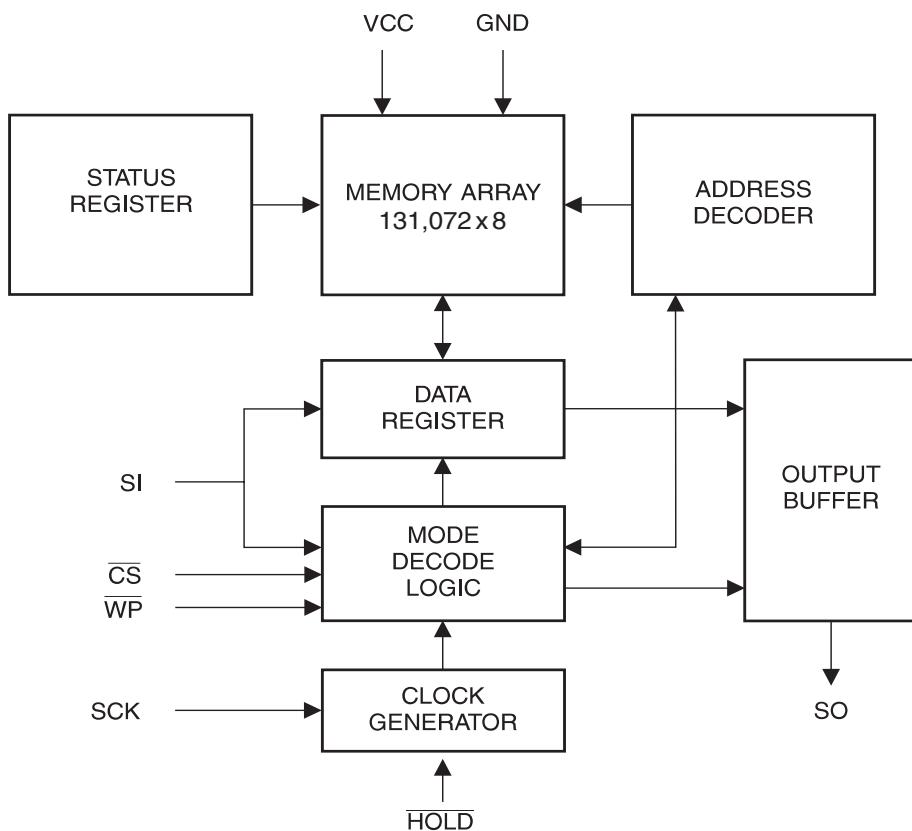
Table 2. Pin Capacitance[1]
Applicable over recommended operating range from T_A = 25°C, f = 1.0 MHz, V_{CC} = +5.0V (unless otherwise noted)

Symbol	Test Conditions	Max	Units	Conditions
C_{OUT}	Output Capacitance (SO)	8	pF	V_{OUT} = 0V
C_{IN}	Input Capacitance ($\overline{CS}$, SCK, SI, $\overline{WP}$, $\overline{HOLD}$)	6	pF	V_{IN} = 0V

Note: 1.   This parameter is characterized and is not 100% tested.

Table 3. DC Characteristics
Applicable over recommended operating range from: T_{AI} = -40°C to +85°C, V_{CC} = +2.7V to +5.5V,
T_{AC} = 0°C to +70°C, V_{CC} = +2.7V to +5.5V (unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Typ	Max	Units
V_{CC1}	Supply Voltage			2.7		5.5	V
V_{CC2}	Supply Voltage			4.5		5.5	V
I_{CC1}	Supply Current	V_{CC} = 5.0V at 1 MHz, SO = Open Read			2.0	5.0	mA
I_{CC2}	Supply Current	V_{CC} = 5.0V at 2 MHz, SO = Open Write			4.0	7.0	mA
I_{SB1}	Standby Current	V_{CC} = 2.7V, $\overline{CS}$ = V_{CC}			0.2	3.0	µA
I_{SB2}	Standby Current	V_{CC} = 5.0V, $\overline{CS}$ = V_{CC}			2.0	7.0	µA
I_{IL}	Input Leakage	V_{IN} = 0V to V_{CC}		-3.0		3.0	µA
I_{OL}	Output Leakage	V_{IN} = 0V to V_{CC}, T_{AC} = 0°C to 70°C		-3.0		3.0	µA
V_{IL}[1]	Input Low Voltage			-0.6		V_{CC} x 0.3	V
V_{IH}[1]	Input High Voltage			V_{CC} x 0.7		V_{CC} + 0.5	V
V_{OL1}	Output Low Voltage	4.5V ≤ V_{CC} ≤ 5.5V	I_{OL} = 3.0 mA			0.4	V
V_{OH1}	Output High Voltage		I_{OH} = -1.6 mA	V_{CC} - 0.8			V

Note: 1. V_{IL} and V_{IH} max are reference only and are not tested.

Table 4. AC Characteristics
Applicable over recommended operating range from T_A = -40°C to +85°C, V_{CC} = As Specified,
C_L = 1 TTL Gate and 100 pF (unless otherwise noted)

Symbol	Parameter	Voltage	Min	Max	Units
f_{SCK}	SCK Clock Frequency	4.5 - 5.5 2.7 - 5.5	0 0	2.1 1.0	MHz
t_{RI}	Input Rise Time	4.5 - 5.5 2.7 - 5.5		2 2	μs
t_{FI}	Input Fall Time	4.5 - 5.5 2.7 - 5.5		2 2	μs
t_{WH}	SCK High Time	4.5 - 5.5 2.7 - 5.5	200 400		ns
t_{WL}	SCK Low Time	4.5 - 5.5 2.7 - 5.5	200 400		ns
t_{CS}	$\overline{CS}$ High Time	4.5 - 5.5 2.7 - 5.5	250 500		ns
t_{CSS}	$\overline{CS}$ Setup Time	4.5 - 5.5 2.7 - 5.5	100 250		ns
t_{CSH}	$\overline{CS}$ Hold Time	4.5 - 5.5 2.7 - 5.5	150 250		ns
t_{SU}	Data In Setup Time	4.5 - 5.5 2.7 - 5.5	30 50		ns
t_H	Data In Hold Time	4.5 - 5.5 2.7 - 5.5	50 50		ns
t_{HD}	$\overline{Hold}$ Setup Time	4.5 - 5.5 2.7 - 5.5	100 100		ns
t_{CD}	$\overline{Hold}$ Hold Time	4.5 - 5.5 2.7 - 5.5	200 300		ns
t_V	Output Valid	4.5 - 5.5 2.7 - 5.5	0 0	200 400	ns
t_{HO}	Output Hold Time	4.5 - 5.5 2.7 - 5.5	0 0		ns
t_{LZ}	$\overline{Hold}$ to Output Low Z	4.5 - 5.5 2.7 - 5.5	0 0	100 200	ns
t_{HZ}	$\overline{Hold}$ to Output High Z	4.5 - 5.5 2.7 - 5.5		100 200	ns
t_{DIS}	Output Disable Time	4.5 - 5.5 2.7 - 5.5		200 250	ns
t_{WC}	Write Cycle Time	4.5 - 5.5 2.7 - 5.5		5 10	ms
Endurance[1]	5.0V, 25°C, Page Mode	4.5 - 5.5 2.7 - 5.5	100K		Write Cycles

Note: 1. This parameter is characterized and is not 100% tested.

Serial Interface Description

MASTER: The device that generates the serial clock.

SLAVE: Because the serial clock pin (SCK) is always an input, the AT25P1024 always operates as a slave.

TRANSMITTER/RECEIVER: The AT25P1024 has separate pins designated for data transmission (SO) and reception (SI).

MSB: The Most Significant Bit (MSB) is the first bit transmitted and received.

SERIAL OP-CODE: After the device is selected with $\overline{CS}$ going low, the first byte will be received. This byte contains the op-code that defines the operations to be performed.

INVALID OP-CODE: If an invalid op-code is received, no data will be shifted into the AT25P1024, and the serial output pin (SO) will remain in a high impedance state until the falling edge of $\overline{CS}$ is detected again. This will reinitialize the serial communication.

CHIP SELECT: The AT25P1024 is selected when the $\overline{CS}$ pin is low. When the device is not selected, data will not be accepted via the SI pin, and the serial output pin (SO) will remain in a high impedance state.

HOLD: The $\overline{HOLD}$ pin is used in conjunction with the $\overline{CS}$ pin to select the AT25P1024. When the device is selected and a serial sequence is underway, $\overline{HOLD}$ can be used to pause the serial communication with the master device without resetting the serial sequence. To pause, the $\overline{HOLD}$ pin must be brought low while the SCK pin is low. To resume serial communication, the $\overline{HOLD}$ pin is brought high while the SCK pin is low (SCK may still toggle during $\overline{HOLD}$). Inputs to the SI pin will be ignored while the SO pin is in the high impedance state.

WRITE PROTECT: The write protect pin ($\overline{WP}$) will allow normal read/write operations when held high. When the $\overline{WP}$ pin is brought low and WPEN bit is "1", all write operations to the status register are inhibited. $\overline{WP}$ going low while $\overline{CS}$ is still low will interrupt a write to the status register. If the internal write cycle has already been initiated, $\overline{WP}$ going low will have no effect on any write operation to the status register. The $\overline{WP}$ pin function is blocked when the WPEN bit in the status register is "0". This will allow the user to install the AT25P1024 in a system with the $\overline{WP}$ pin tied to ground and still be able to write to the status register. All $\overline{WP}$ pin functions are enabled when the WPEN bit is set to "1".

Figure 2. SPI Serial Interface
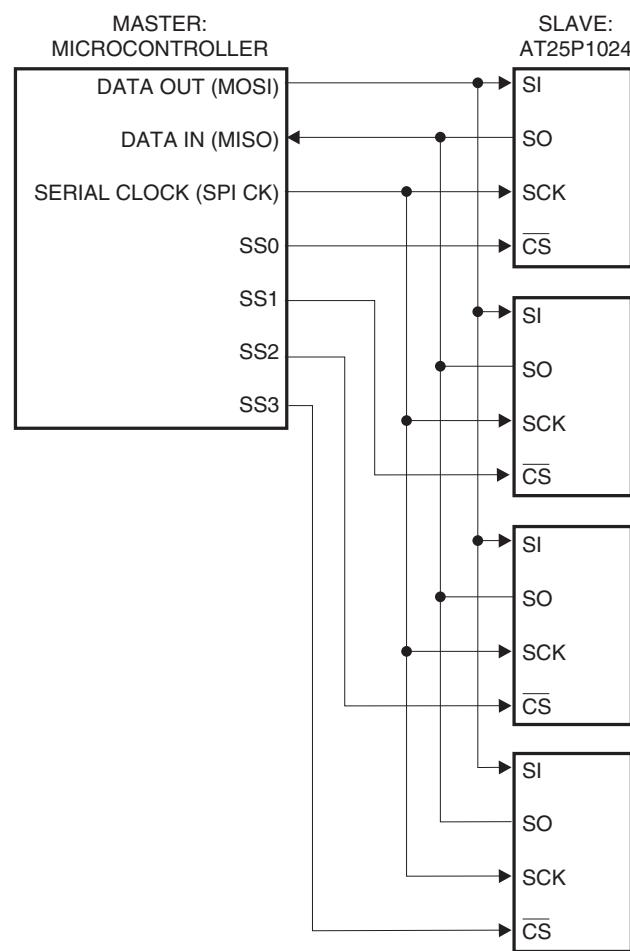
Functional Description

The AT25P1024 is designed to interface directly with the synchronous serial peripheral interface (SPI) of the 6800 type series of microcontrollers.

The AT25P1024 utilizes an 8-bit instruction register. The list of instructions and their operation codes are contained in Table 5. All instructions, addresses, and data are transferred with the MSB first and start with a high-to-low transition.

Table 5. Instruction Set for the AT25P1024

Instruction Name	Instruction Format	Operation
WREN	0000 X110	Set Write Enable Latch
WRDI	0000 X100	Reset Write Enable Latch
RDSR	0000 X101	Read Status Register
WRSR	0000 X001	Write Status Register
READ	0000 X011	Read Data from Memory Array
WRITE	0000 X010	Write Data to Memory Array

WRITE ENABLE (WREN): The device will power up in the write disable state when V_{CC} is applied. All programming instructions must therefore be preceded by a Write Enable instruction.

WRITE DISABLE (WRDI): To protect the device against inadvertent writes, the Write Disable instruction disables all programming modes. The WRDI instruction is independent of the status of the $\overline{WP}$ pin.

READ STATUS REGISTER (RDSR): The Read Status Register instruction provides access to the status register. The Ready/Busy and Write Enable status of the device can be determined by the RDSR instruction. Similarly, the block write protection bits indicate the extent of protection employed. These bits are set by using the WRSR instruction.

Table 6. Status Register Format

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
WPEN	X	X	X	BP1	BP0	WEN	$\overline{RDY}$

Table 7. Read Status Register Bit Definition

Bit	Definition
Bit 0 ($\overline{\text{RDY}}$)	Bit 0 = "0" ($\overline{\text{RDY}}$) indicates the device is ready. Bit 0 = "1" indicates the write cycle is in progress.
Bit 1 (WEN)	Bit 1 = "0" indicates the device *is not* write enabled. Bit 1 = "1" indicates the device is write enabled.
Bit 2 (BP0)	See Table 8.
Bit 3 (BP1)	See Table 8.
Bits 4-6 are "0"s when device is not in an internal write cycle.	
Bit 7 (WPEN)	See Table 9.
Bits 0-7 are "1"s during an internal write cycle.	

WRITE STATUS REGISTER (WRSR): The WRSR instruction allows the user to select one of four levels of protection. The AT25P1024 is divided into four array segments. Top quarter (1/4), top half (1/2), or all of the memory segments can be protected. Any of the data within any selected segment will therefore be read only. The block write protection levels and corresponding status register control bits are shown in Table 8.

The three bits, BP0, BP1, and WPEN are nonvolatile cells that have the same properties and functions as the regular memory cells (e.g. WREN, t_{WC}, RDSR).

Table 8. Block Write Protect Bits

	Status Register Bits		Array Addresses Protected
Level	BP1	BP0	AT25P1024
0	0	0	None
1(1/4)	0	1	01800 - 01FFFF
2(1/2)	1	0	010000 - 01FFFF
3(All)	1	1	0000 - 01FFFF

The WRSR instruction also allows the user to enable or disable the write protect ($\overline{\text{WP}}$) pin through the use of the write protect enable (WPEN) bit. Hardware write protection is enabled when the $\overline{\text{WP}}$ pin is low and the WPEN bit is "1". Hardware write protection is disabled when *either* the $\overline{\text{WP}}$ pin is high or the WPEN bit is "0". When the device is hardware write protected, writes to the Status Register, including the block protect bits and the WPEN bit, and the block-protected sections in the memory array are disabled. Writes are only allowed to sections of the memory which are not block-protected.

NOTE: When the WPEN bit is hardware write protected, it cannot be changed back to "0", as long as the $\overline{\text{WP}}$ pin is held low.

Table 9. WPEN Operation

WPEN	WP	WEN	Protected Blocks	Unprotected Blocks	Status Register
0	X	0	Protected	Protected	Protected
0	X	1	Protected	Writable	Writable
1	Low	0	Protected	Protected	Protected

Table 9. WPEN Operation (Continued)

WPEN	WP	WEN	Protected Blocks	Unprotected Blocks	Status Register
1	Low	1	Protected	Writable	Protected
X	High	0	Protected	Protected	Protected
X	High	1	Protected	Writable	Writable

READ SEQUENCE (READ):   Reading the AT25P1024 via the SO (Serial Output) pin requires the following sequence. After the $\overline{CS}$ line is pulled low to select a device, the READ op-code is transmitted via the SI line followed by the byte address to be read (Refer to Table 10). Upon completion, any data on the SI line will be ignored. The data (D7-D0) at the specified address is then shifted out onto the SO line. If only one byte is to be read, the $\overline{CS}$ line should be driven high after the data comes out. The read sequence can be continued since the byte address is automatically incremented and data will continue to be shifted out. When the highest address is reached, the address counter will roll over to the lowest address allowing the entire memory to be read in one continuous read cycle.

WRITE SEQUENCE (WRITE):   In order to program the AT25P1024, two separate instructions must be executed. First, the device *must be write enabled* via the WREN instruction. Then a Write instruction may be executed. Also, the address of the memory location(s) to be programmed must be outside the protected address field location selected by the block write protection level. During an internal write cycle, all commands will be ignored except the RDSR instruction.

A Write Instruction requires the following sequence. After the $\overline{CS}$ line is pulled low to select the device, the Write op-code is transmitted via the SI line followed by the byte address and the data (D7-D0) to be programmed (Refer to Table 9). Programming will start after the $\overline{CS}$ pin is brought high. The low-to-high transition of the $\overline{CS}$ pin must occur during the SCK low time immediately after clocking in the D0 (LSB) data bit.

The Ready/Busy status of the device can be determined by initiating a Read Status Register (RDSR) Instruction. If Bit 0 = "1", the write cycle is still in progress. If Bit 0 = "0", the write cycle has ended. Only the Read Status Register instruction is enabled during the write programming cycle.

The AT25P1024 is capable of a 128-byte Page Write operation ONLY. Content of the page in the array will not be guaranteed if less than 128 bytes of data is received (byte operation is not supported). After each byte of data is received, the seven low order address bits are internally incremented by one; the high order bits of the address will remain constant. If more than 128 bytes of data are transmitted, the address counter will roll over and the previously written data will be overwritten. The AT25P1024 is automatically returned to the write disable state at the completion of a write cycle.

NOTE: If the device is not Write enabled (WREN), the device will ignore the Write instruction and will return to the standby state, when $\overline{CS}$ is brought high. A new CS falling edge is required to re-initiate the serial communication.

Table 10. Address Key

Address	AT25P1024
A_N	A_{16} - A_0
Don't Care Bits	A_{23} - A_{17}

Timing Diagrams (for SPI Mode 0 (0, 0))

**Figure 3.** Synchronous Data Timing
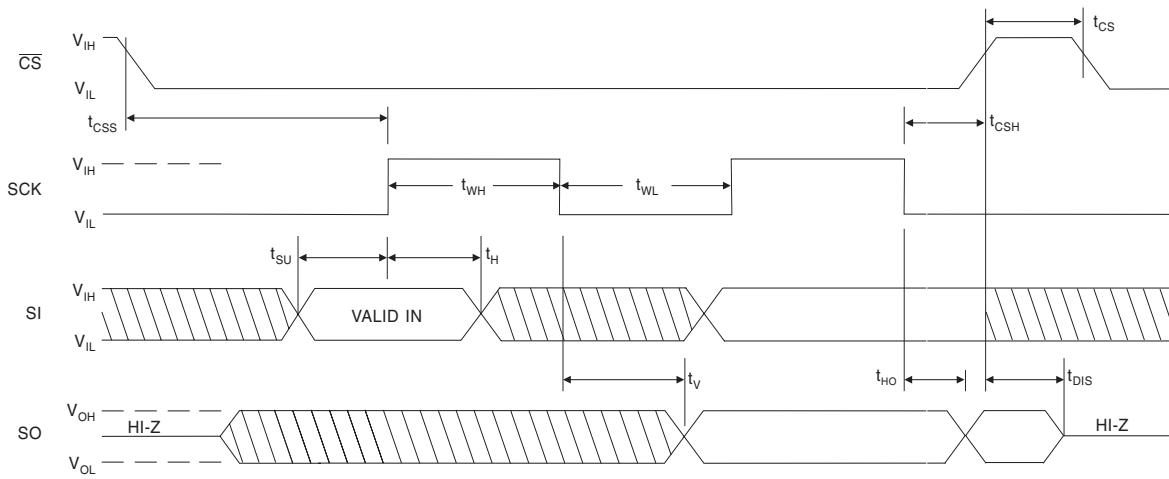
**Figure 4.** WREN Timing
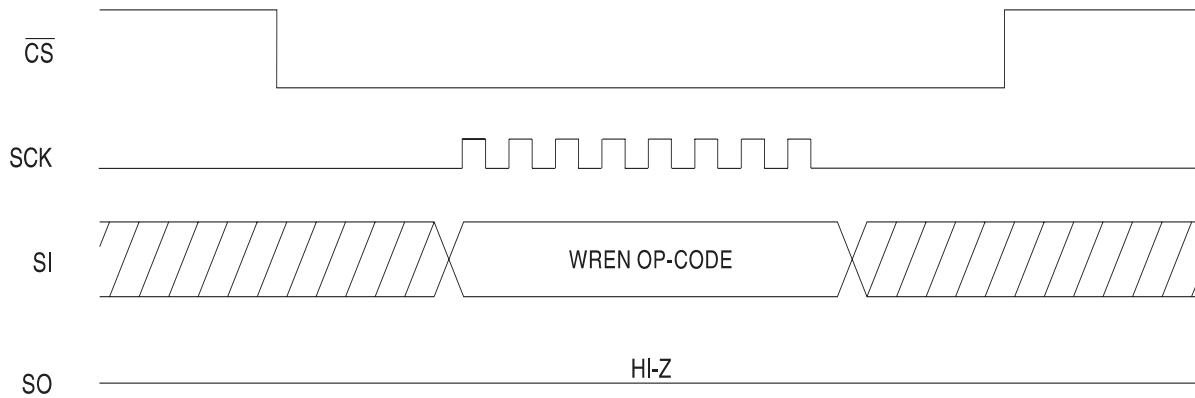

Figure 5. WRDI Timing
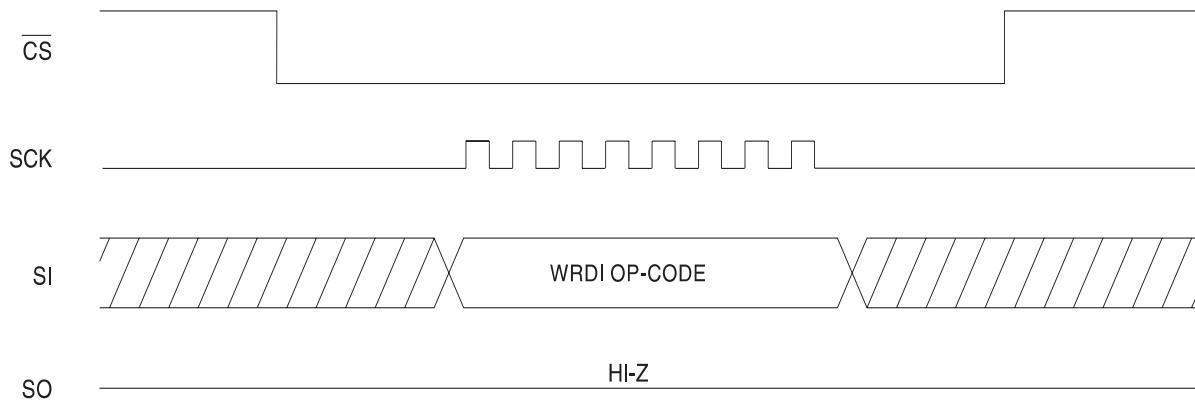
Figure 6. RDSR Timing
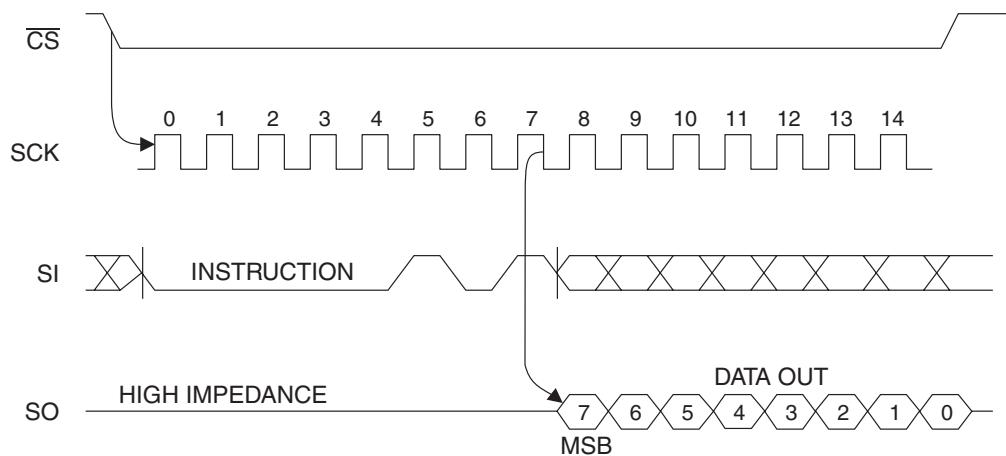
**Figure 7.** WRSR Timing
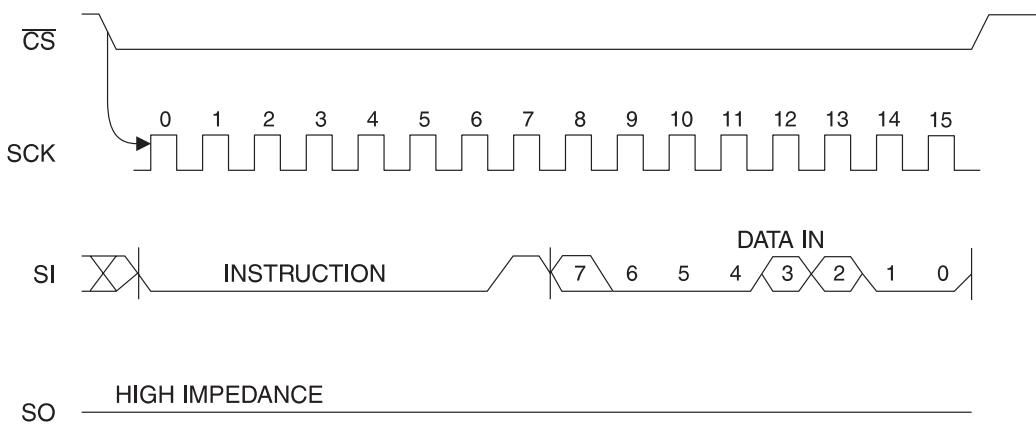
**Figure 8.** READ Timing
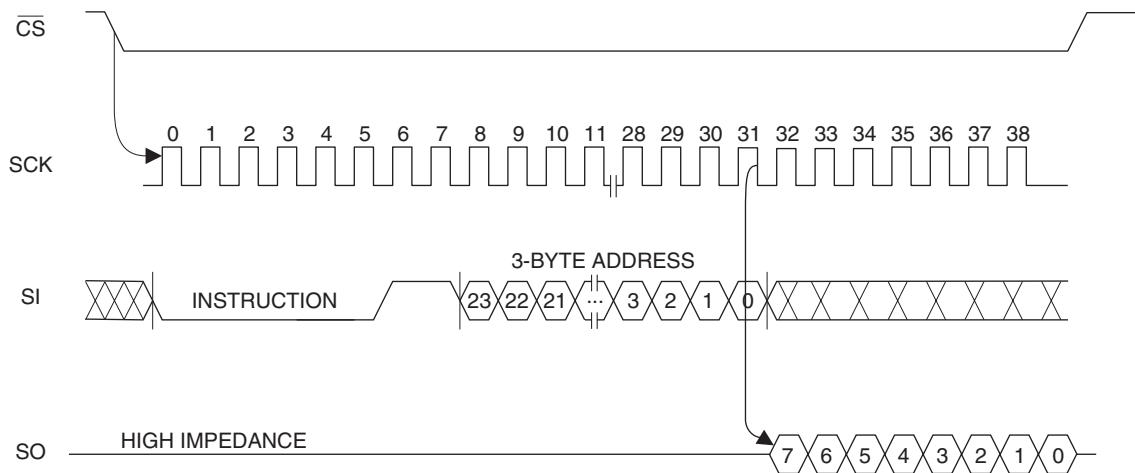
Figure 9. WRITE Timing
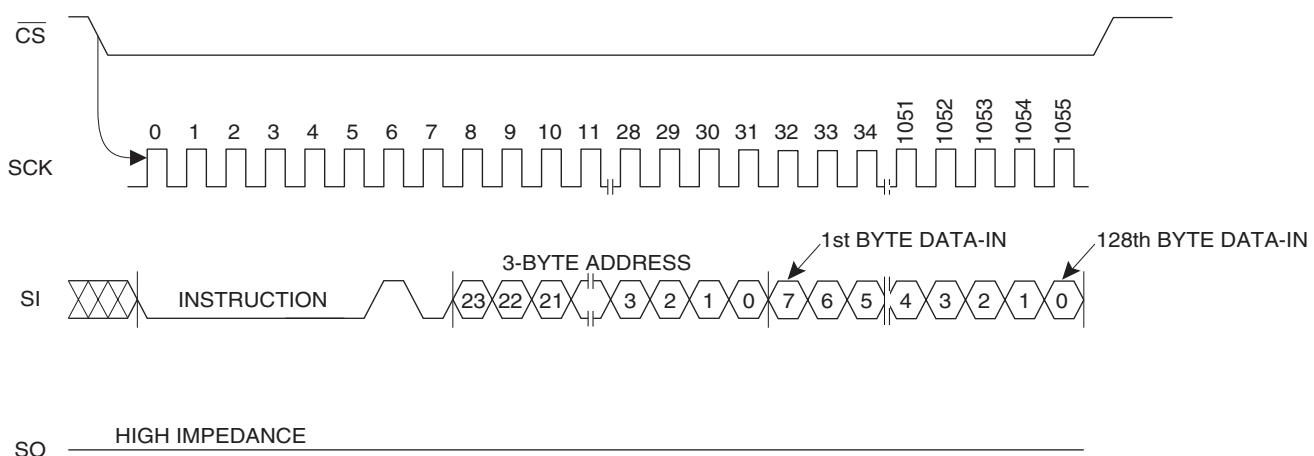
Figure 10. HOLD Timing
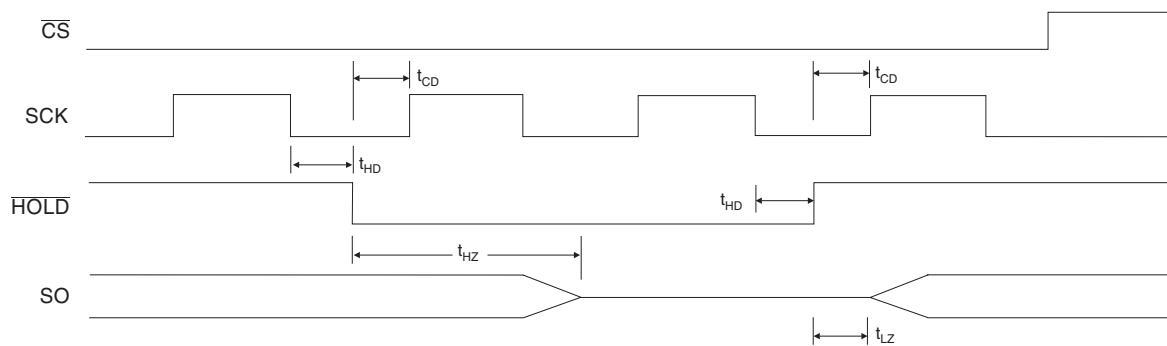
Ordering Information[1]

Ordering Code	Package	Operation Range
AT25P1024C1-10CI-2.7 AT25P1024W1-10SI-2.7	8C1 20S2	Industrial (-40°C to 85°C)
AT25P1024C1-10CU-2.7[2] AT25P1024W1-10SU-2.7[2]	8C1 20S2	Lead-Free\Halogen-Free Industrial Temperature (-40°C to 85°C)

Notes: 1. For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC Characteristics tables.

2. "U" designates Green Package & RoHS Compliant.

Package Type		
8C1	8-pad, 0.300" Wide, Leadless Array Package (LAP)	
20S2	20-lead, 0.300" Wide, Plastic Gull Wing Small Outline Package (JEDEC SOIC)	
Options		
-2.7	Low-voltage (2.7V to 5.5V)	

Packaging Information

8C1 – LAP

Marked Pin1 Indentifier

E

D

Top View

A

A1

Side View

0.10 mm
TYP

L1

Pin1 Corner

8   1

e

7   2

6   3

b

5   4

e1   L
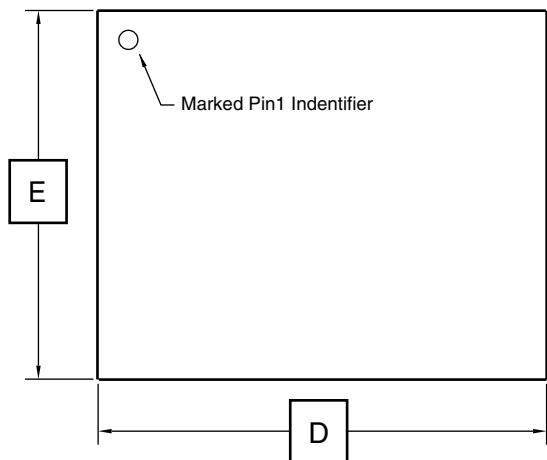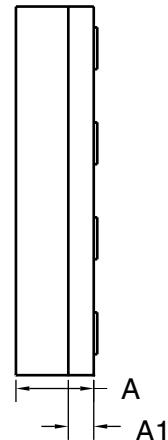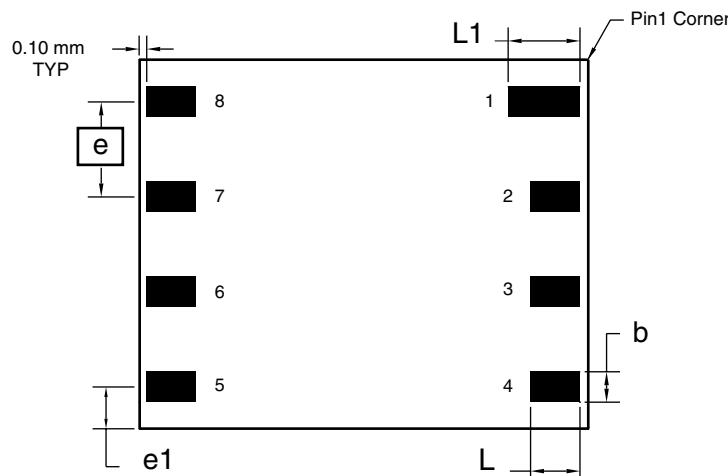
Bottom View

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.94	1.04	1.14	
A1	0.30	0.34	0.38	
b	0.36	0.41	0.46	1
D	7.90	8.00	8.10	
E	4.90	5.00	5.10	
e		1.27 BSC		
e1		0.60 REF		
L	0.62	.0.67	0.72	1
L1	0.92	0.97	1.02	1

Note: 1. Metal Pad Dimensions.
       2. All exposed metal area shall have the following finished platings.
          Ni: 0.0005 to 0.015 mm
          Au: 0.0005 to 0.001 mm

11/8/04

AIMEL 1150 E.Cheyenne Mtn Blvd. Colorado Springs, CO 80906	**TITLE** **8CN1**, 8-lead (8 x 5 x 1.04 mm Body), Lead Pitch 1.27 mm, Leadless Array Package (LAP)	**DRAWING NO.** 8CN1	**REV.** B

20S2 – JEDEC SOIC
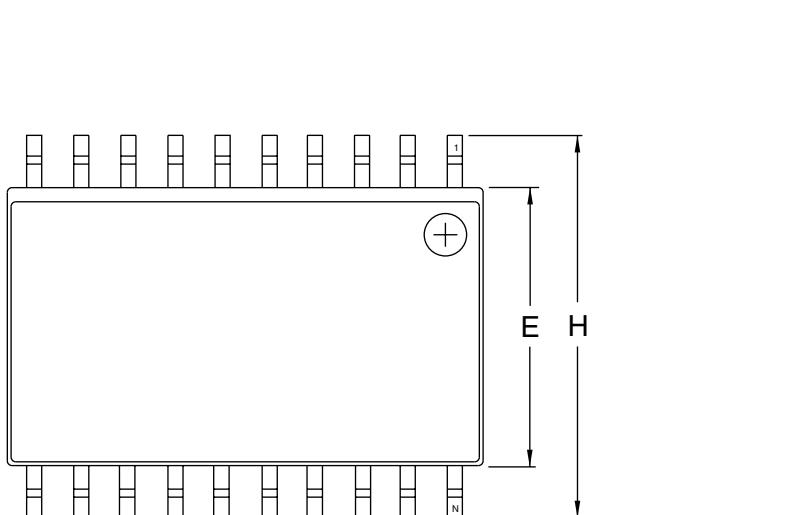
Top View
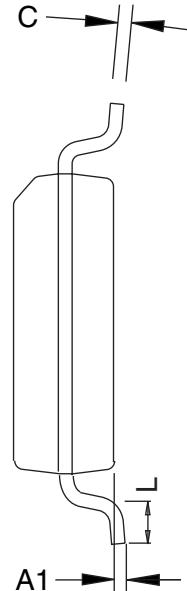
Side View

End View
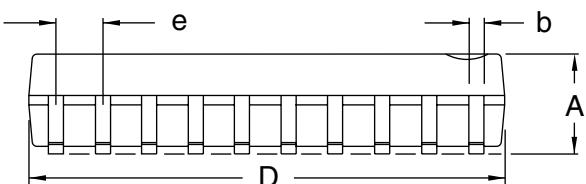
COMMON DIMENSIONS
(Unit of Measure = inches)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.0926		0.1043	
A1	0.0040		0.0118	
b	0.0130		0.0200	4
C	0.0091		0.0125	
D	0.4961		0.5118	1
E	0.2914		0.2992	2
H	0.3940		0.4190	
L	0.0160		0.050	3
e	0.050 BSC			

Notes: 1. This drawing is for general information only; refer to JEDEC Drawing MS-013, Variation AC for additional information.
2. Dimension "D" does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006") per side.
3. Dimension "E" does not include inter-lead Flash or protrusion. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010") per side.
4. "L" is the length of the terminal for soldering to a substrate.
5. The lead width "b", as measured 0.36 mm (0.014") or greater above the seating plane, shall not exceed a maximum value of 0.61 mm (0.024") per side.

1/9/02

	2325 Orchard Parkway San Jose, CA 95131	**TITLE** **20S2**, 20-lead, 0.300" Wide Body, Plastic Gull Wing Small Outline Package (SOIC)	**DRAWING NO.** 20S2	**REV.** A

Revision History

Doc. Rev.	Comments
1082I	Added Note 'Not Recommended for new design; please refer to AT25FS010 datasheet' to first page.

Atmel Corporation

2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 487-2600

Regional Headquarters

Europe
Atmel Sarl
Route des Arsenaux 41
Case Postale 80
CH-1705 Fribourg
Switzerland
Tel: (41) 26-426-5555
Fax: (41) 26-426-5500

Asia
Room 1219
Chinachem Golden Plaza
77 Mody Road Tsimshatsui
East Kowloon
Hong Kong
Tel: (852) 2721-9778
Fax: (852) 2722-1369

Japan
9F, Tonetsu Shinkawa Bldg.
1-24-8 Shinkawa
Chuo-ku, Tokyo 104-0033
Japan
Tel: (81) 3-3523-3551
Fax: (81) 3-3523-7581

Atmel Operations

Memory
2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

Microcontrollers
2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

La Chantrerie
BP 70602
44306 Nantes Cedex 3, France
Tel: (33) 2-40-18-18-18
Fax: (33) 2-40-18-19-60

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